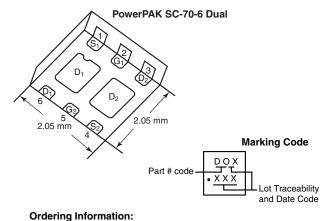
Vishay Siliconix

### Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) Max.	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)		
	0.065 at V <sub>GS</sub> = - 10 V	- 4.5 <sup>a</sup>			
- 30	0.080 at V <sub>GS</sub> = - 6 V	- 4.5 <sup>a</sup>	4.1 nC		
	0.100 at V <sub>GS</sub> = - 4.5 V	- 4.5 <sup>a</sup>			



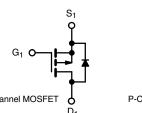
SiA931DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

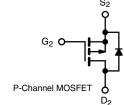
### **FEATURES**

- TrenchFET<sup>®</sup> Gen III Power MOSFET
- Thermally Enhanced PowerPAK<sup>®</sup> SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
- 100 % R<sub>g</sub> Tested
- FREE Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

#### APPLICATIONS

- Smart Phones, Tablet PCs, Mobile Computing:
  - Battery Switches
  - Load Switches
  - Power Management
  - DC/DC Converters





P-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 30	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20		
	T <sub>C</sub> = 25 °C		- 4.5 <sup>a</sup>		
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	- 4.5 <sup>a</sup>		
Continuous Drain Current (1) = 150°C)	T <sub>A</sub> = 25 °C	D	- 4.3 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		- 3.4 <sup>b, c</sup>	A	
Pulsed Drain Current (t = 300 µs)		I <sub>DM</sub>	- 28	1	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I <sub>S</sub>	- 4.5 <sup>a</sup>		
	T <sub>A</sub> = 25 °C	'5	- 1.6 <sup>b, c</sup>		
Maximum Power Dissipation	T <sub>C</sub> = 25 °C		7.8		
	T <sub>C</sub> = 70 °C	PD	5	w	
	T <sub>A</sub> = 25 °C	' D	1.9 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		1.2 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	52	65	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	12.5	16		

Notes: a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

Maximum under steady state conditions is 110 °C/W. f.

Document Number: 62859 For technical questions, contact: pmostechsupport@vishav.com S13-1163-Rev. A, 13-May-13



### Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static					1	1	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_{D} = -250 \mu A$	- 30			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	1 050 4		- 24		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = - 250 μΑ		3.4			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA			- 2.2	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current		V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1	<u> </u>	
	I <sub>DSS</sub>	$V_{DS}$ = - 30 V, $V_{GS}$ = 0 V, $T_{J}$ = 55 °C			- 10	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le$ - 5 V, $V_{GS}$ = - 10 V	- 10			А	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3 A		0.052	0.065		
	R <sub>DS(on)</sub>			0.063	0.080	Ω	
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 2 A		0.077	0.100	1	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 3 A		8		S	
Dynamic <sup>b</sup>						<u> </u>	
Input Capacitance	C <sub>iss</sub>			445		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		55			
Reverse Transfer Capacitance	C <sub>rss</sub>			45			
-		V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 4 A		8.5	13	+	
Total Gate Charge	Qg			4.1	6.2	nC	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 4 A		1.2			
Gate-Drain Charge	Q <sub>gd</sub>			1.5			
Gate Resistance	R <sub>q</sub>	f = 1 MHz	1.1	5.5	11	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			23	45		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_{I}$ = 5 $\Omega$		18	35	- ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 3 Å, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		17	35		
Fall Time	t <sub>f</sub>	-		5	10		
Turn-On Delay Time	t <sub>d(on)</sub>			8	15		
Rise Time	t <sub>r</sub>	$V_{DD} = -15 V, R_1 = 5 \Omega$		5	10		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 3 A, $V_{GEN}$ = - 10 V, $R_q$ = 1 $\Omega$		20	40		
Fall Time	t <sub>f</sub>	Ğ		5	10		
Drain-Source Body Diode Characterist	ics					<u> </u>	
Continuous Source-Drain Diode Current	ا <sub>S</sub>	T <sub>C</sub> = 25 °C			- 4.5		
Pulse Diode Forward Current	I <sub>SM</sub>				- 15	A	
Body Diode Voltage	V <sub>SD</sub>	$I_{\rm S}$ = - 3 A, $V_{\rm GS}$ = 0 V		- 0.9	- 1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			15	30	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	$\neg$		8	20	nC	
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F$ = - 3 A, dl/dt = 100 A/µs, T <sub>J</sub> = 25 °C		10		ns	
Reverse Recovery Rise Time	t <sub>b</sub>			5			

Notes:

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

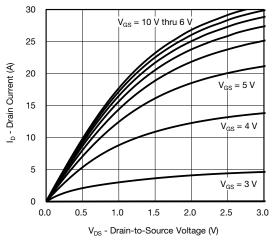
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Document Number: 62859 S13-1163-Rev. A, 13-May-13

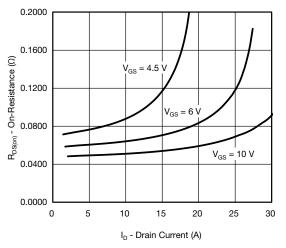


### SiA931DJ Vishay Siliconix

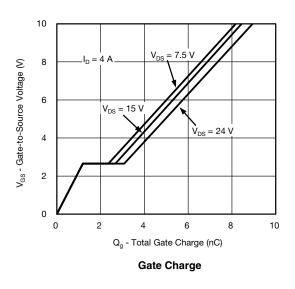
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

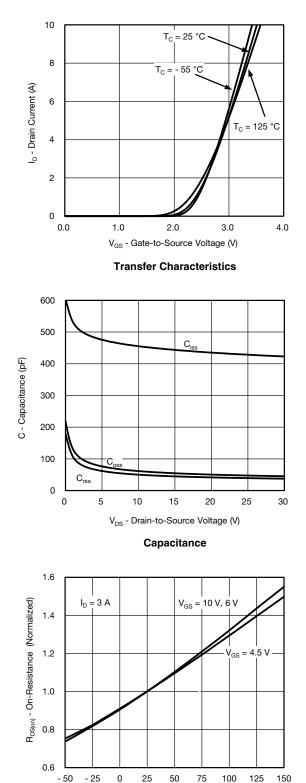






**On-Resistance vs. Drain Current and Gate Voltage** 





T<sub>J</sub> - Junction Temperature (°C) On-Resistance vs. Junction Temperature

Document Number: 62859 S13-1163-Rev. A, 13-May-13 For technical questions, contact: pmostechsupport@vishay.com

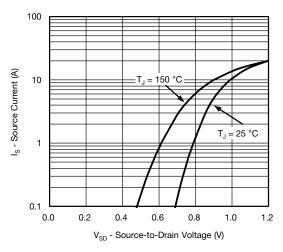
www.vishay.com

3

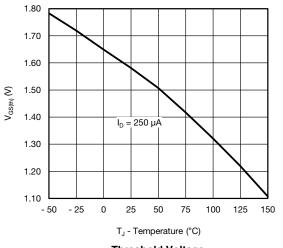
### **Vishay Siliconix**



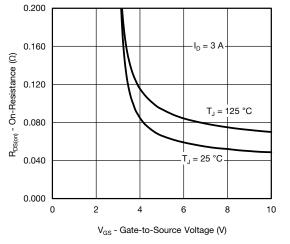
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



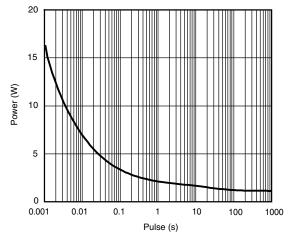
Soure-Drain Diode Forward Voltage



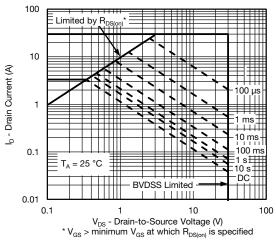




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

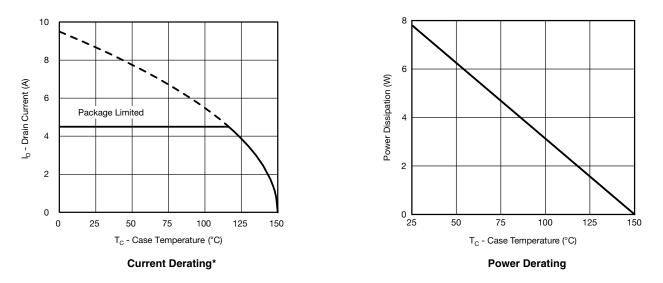


Safe Operating Area, Junction-to-Ambient

Document Number: 62859 S13-1163-Rev. A, 13-May-13



#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

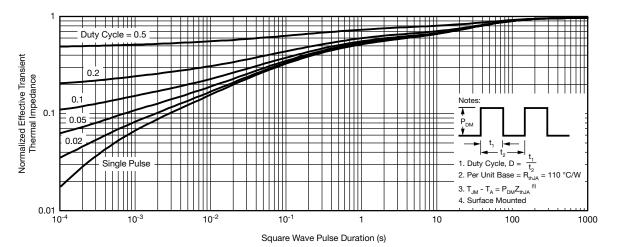


\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

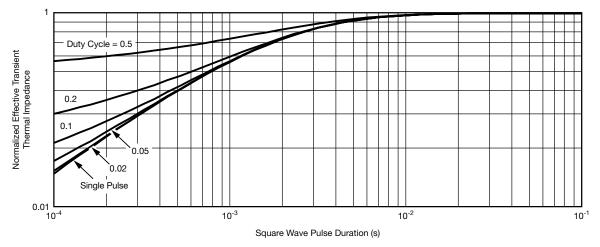


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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

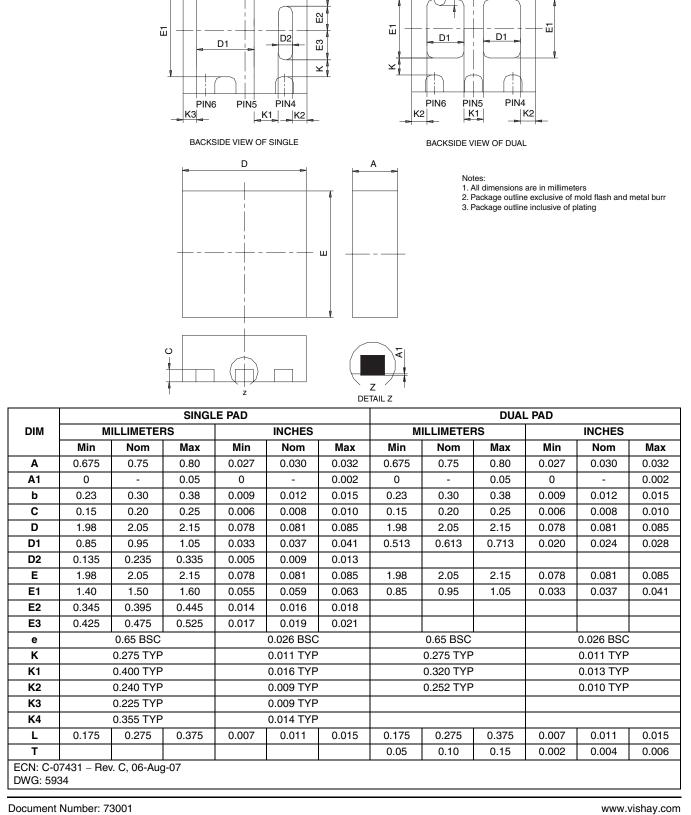


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?62859">www.vishay.com/ppg?62859</a>.

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Document Number: 62859 S13-1163-Rev. A, 13-May-13



### PowerPAK<sup>®</sup> SC70-6L

VISHA

# b PIN2 PIN1 PIN3 \_ ₹



b

PIN3

\_\_ ₿

PIN2

PIN1

¥

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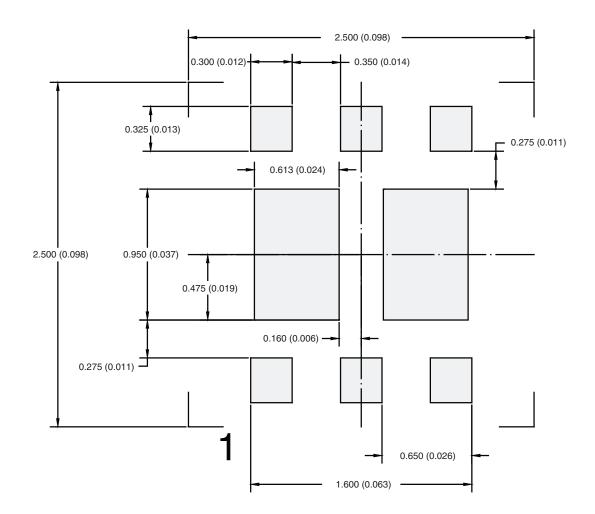
<sup>1</sup> 

## **Application Note 826**

Vishay Siliconix



#### **RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual**



Dimensions in mm (inches)

Return to Index



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